



ALPHA & OMEGA
SEMICONDUCTOR

AON7406

N-Channel Enhancement Mode Field Effect Transistor

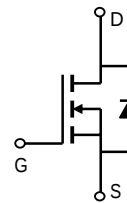
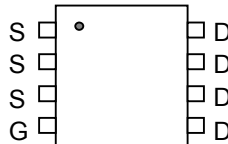
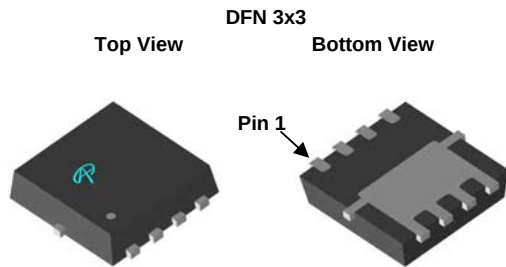


General Description

The AON7406 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use in SMPS and general purpose applications. *Standard Product AON7406 is Pb-free (meets ROHS & Sony 259 specifications).*

Features

V_{DS} (V) = 30V
 I_D = 11A (V_{GS} = 10V)
 $R_{DS(ON)} < 15m\Omega$ (V_{GS} = 10V)
 $R_{DS(ON)} < 23.5m\Omega$ (V_{GS} = 4.5V)



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^{B,H}	I_D	20	A
$T_C=25^\circ\text{C}$		20	
$T_C=100^\circ\text{C}$	I_{DSM}	11	
Pulsed Drain Current ^C		8.8	
Continuous Drain Current ^G	P_D	27	W
$T_A=25^\circ\text{C}$		11	
$T_A=70^\circ\text{C}$	P_{DSM}	3.1	
Power Dissipation ^B		2	
Power Dissipation ^A			
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	30	40	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A		60	75	$^\circ\text{C/W}$
Maximum Junction-to-Case ^D	$R_{\theta JC}$	4	4.5	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1	1.6	3	V
I _{D(ON)}	On state drain current	V _{GS} =10V, V _{DS} =5V	50			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =11A T _J =125°C		12.5 17.5	15 21	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =10A		19		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.73	1	V
I _S	Maximum Body-Diode Continuous Current				3	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		955	1200	pF
C _{oss}	Output Capacitance			145		pF
C _{rss}	Reverse Transfer Capacitance			112		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		0.5	0.85	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =10A		17	24	nC
Q _g (4.5V)	Total Gate Charge			9	12	nC
Q _{gs}	Gate Source Charge			3.4		nC
Q _{gd}	Gate Drain Charge			4.7		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =15V, R _L =1.5Ω, R _{GEN} =3Ω		5		ns
t _r	Turn-On Rise Time			6		ns
t _{D(off)}	Turn-Off DelayTime			19		ns
t _f	Turn-Off Fall Time			4.5		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =11A, dI/dt=100A/μs		19	25	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =11A, dI/dt=100A/μs		9		nC

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using <300 ms pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

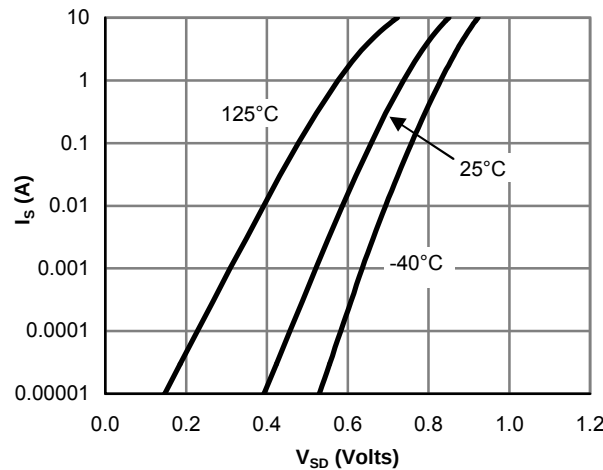
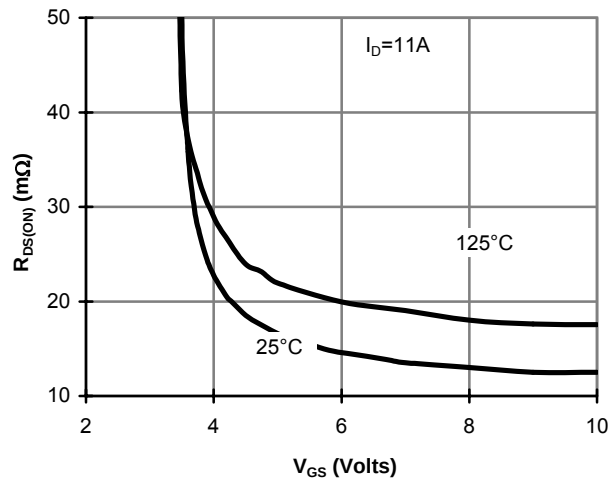
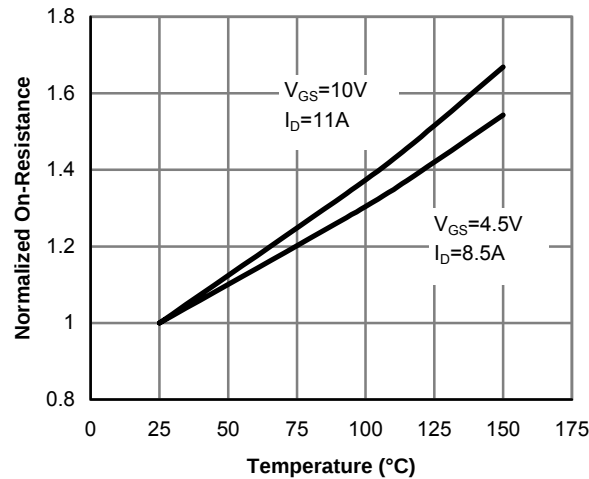
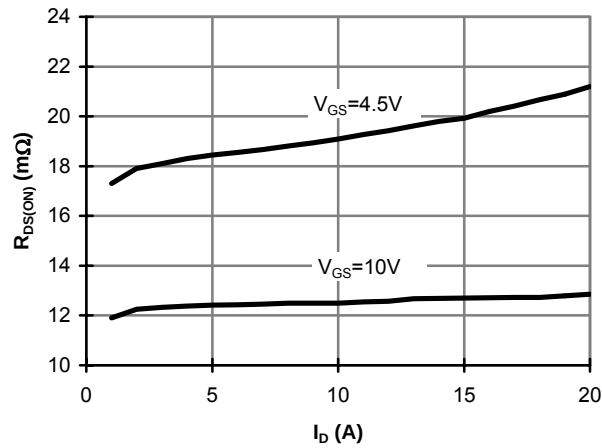
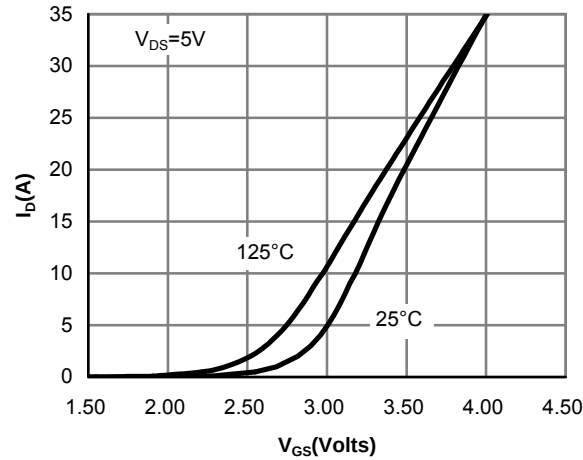
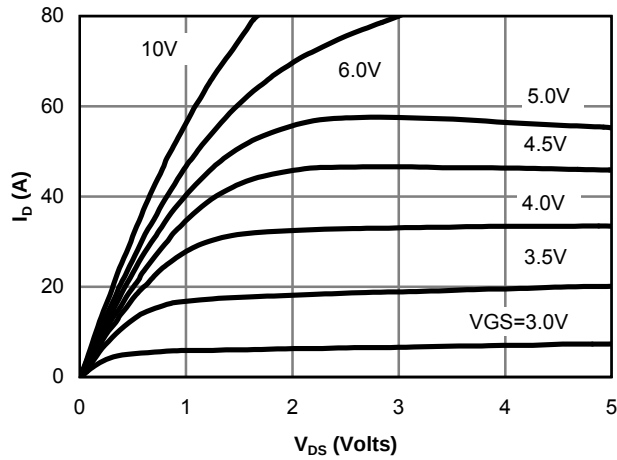
F: The current rating is based on the t ≤ 10s junction to ambient thermal resistance rating.

G: The maximum current rating is limited by bond-wires.

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